

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 05770-132001	Application No. 09/617,518
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Fritzemeier et al.	
		Filing Date July 14, 2000	Group Art Unit 2811 #4

U.S. Patent Documents							
Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
ke	AA	5,866,252	02/02/1999	de Rochemont et al.	428	373	
W	AB	5,449,659	09/12/1995	Garrison et al.	505	330	

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
ke	AC	WO 99/16941	04/08/1999	PCT				✓
ke	AD	WO 99/17307	04/08/1999	PCT				✓
ke	AF	0 584 410 A1	03/02/1994	EPO				✓

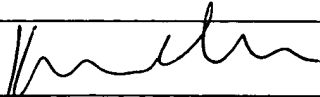
RECEIVED  
JUL 05 2001  
TC 1700

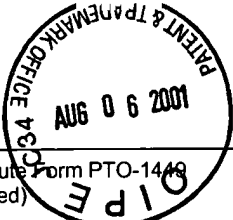
Examiner Signature <i>[Signature]</i>	Date Considered 12/16/01
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 05770-132001	Application No. 09/617,518
<b>Supplemental Information Disclosure Statement by Applicant</b> (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Fritzemeier et al.	
		Filing Date July 14, 2000	Group Art Unit 1751

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
fl	AX	Apicella et al., "The Effects of Surface Contamination On The Biaxially Textured Substrate For YBCO Thick Film Deposition", International Journal of Modern Physics B, Vol. 13, Nos. 9 & 10 (1999) pp 997-1004.
fl	AY	He et al., "Deposition of biaxially-oriented metal and oxide buffer-layer films on textured Ni tapes: new substrates for high-current, high-temperature superconductors", Physica C, 275 (1997) 155-161.
fl	AZ	McIntyre et al., "Epitaxial nucleation and growth of chemically derived $\text{Ba}_2\text{YCu}_3\text{O}_{7-x}$ thin films on (001) $\text{SrTiO}_3$ ", Journal of Applied Physics, 77 (1995) 15 May, No. 10, pp 5263-5272.
fl	AAA	Boffa et al., "Laser-ablation deposition of $\text{CeO}_2$ thin films on biaxially textured nickel substrates", Physica C 312 (1999) 202-212.
fl	ABB	He et al., "Growth of biaxially oriented conductive $\text{LaNiO}_3$ buffer layers on textured Ni tapes for high- $T_c$ -coated conductors", Physica C 314 (1999) 105-111.
fl	ACC	Sheth et al., "Bench Scale Evaluation of Batch Mode Dip-Coating of Sol-Gel $\text{LaAlO}_3$ Buffer Material", IEEE TRANSACTIONS ON APPLIED SUPERCONDUCTIVITY, Vol. 9, No. 2, June 1999, pp 1514 - 1518.
fl	ADD	Smith et al., "High Critical Current Density Thick MOD-Derived YBCO Films", IEEE TRANSACTIONS ON APPLIED SUPERCONDUCTIVITY, Vol. 9, No. 2, June 1999, pp 1531-1534.
fl	AEE	Beach et al., "SOL-GEL SYNTHESIS OF RARE EARTH ALUMINATE FILMS AS BUFFER LAYERS FOR HIGH $T_c$ SUPERCONDUCTING FILMS", Mat. Res. Soc. Symp. Proc. Vol. 495, 1995, pp 263-270.
fl	AFF	Lee et al., "Alternative Buffer Architectures for High Critical Current Density YBCO Superconducting Deposits on Rolling Assisted Biaxially-Textured Substrates", Jpn. J. Appl. Phys. Vol. 38 (1999) Pt. 2, No. 2B, pp 178-180.
fl	AGG	Paranthaman et al., Growth of biaxially textured $\text{RE}_2\text{O}_3$ buffer layers on rolled-Ni substrates using reactive evaporation for HTS-coated conductors", Supercond. Sci. Techno. 12(1999) 319-315. Printed in the UK.
fl	AHH	Rupich et al., "Growth and Characterization of Oxide Buffer Layers for YBCO Coated Conductors", IEEE TRANSACTIONS ON APPLIED SUPERCONDUCTIVITY, Vol. 9, No. 2, June 1999, pp 1527-1530.
fl	AII	Shoup et al., "Epitaxial Thin Film Growth of Lanthanum and Neodymium Aluminate Films on Roll-Textured Nickel Using a Sol-Gel Method", Journal of the American Ceramic Society, Vol. 81, No. 11, November 1998, pp-3019-3021.
fl	AJJ	"DRY ETCHING for VLSI FABRICATION", vol. 1, eds. S. Wolf and R.N. Tamber, Lattice Press, Sunset Park, CA, pp 539-574 (1986).

Examiner Signature 	Date Considered 12/14/01
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



<b>Substitute Form PTO-1449</b> (Modified)  <b>Second Supplemental Information Disclosure Statement</b> <b>by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 05770-132001	Application No. 09/617,518
	Applicant Fritzemeier et al.		
	Filing Date July 14, 2000	Group Art Unit 1751 #7 2841	

**U.S. Patent Documents**

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
he	AA	4,994,433	02/19/1991	Chiang	505	1	

**Foreign Patent Documents or Published Foreign Patent Applications**

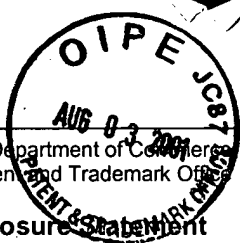
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
he	AB	WO 92/05591	04/02/1992	PCT	—	—		✓
he	AC	0 506 528 A2	09/03/1992	EPO	—	—		✓
he	AD	0 308 869 A2	03/29/1989	EPO	—	—		✓
	AE	0 431 782 A1	06/12/1991	EPO	—	—		✓

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
he	AF	Tanaka et al., "Improvement of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> Single-Crystal Surface by Chemical Etching", Jpn. J. App. Phys. Vol. 38 (1999) pp L731-L733, Part 2, No. 7A, 1 July 1999.
he	AG	Koster et al., "Influence of the surface treatment on the homoepitaxial growth of SrTiO <sub>3</sub> ", Materials Science and Engineering B56 (1998) 209-212.
he	AH	McIntyre et al., "Effect of growth conditions on the properties and morphology of chemically derived epitaxial thin films of Ba <sub>2</sub> YCu <sub>3</sub> O <sub>7-x</sub> on (001) LaAlO <sub>3</sub> ", J. Appl. Phys. 71 (4), 15 February 1992, pp 1868 - 1877.
he	AI	"FABRICATION OF HIGH TEMPERATURE SUPERCONDUCTING FILMS USING PERFLUORO-ORGANOMETALLIC PRECURSORS", IMB Technical Disclosure Bulletin, Vol. 32, No. 5B, October 1989, p 241.

RECEIVED  
AUG 08 2001  
TC 1700

Examiner Signature 	Date Considered 12/16/01
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	



Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 05770-132001	Application No. 09/617,518
		Applicant Fritzemeier et al. #6	
		Filing Date July 14, 2000	Group Art Unit 1751-2841

**Supplemental Information Disclosure Statement**  
by Applicant  
(Use several sheets if necessary)

(37.CFR §1.98(b))

U.S. Patent Documents							
Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
RL	AA	09/617,520 ✓	07/14/2000	Lu et al.			
RL	AB	09/616,570 ✓	07/14/2000	Fritzemeier et al.			
RL	AC	09/500,717 ✓	02/09/2000	Fritzemeier et al.			
RL	AD	09/500,718 ✓	02/09/2000	Malozemoff et al.			
RL	AE	6,027,564	02/22/2000	Fritzemeier et al.			
RL	AF	09/616,566	07/14/2000	Zhang et al.			
RL	AG	09/615,669 ✓	07/14/2000	Buczek et al.			
RL	AH	5,968,877	10/19/1999	Budai et al.	505	237	
RL	AI	5,741,377	04/21/1998	Goyal et al.	148	512	
RL	AJ	5,231,074	07/27/1993	Cima et al.	505	1	
RL	AK	5,073,537	12/17/1991	Hung et al.	505	1	
RL	AL	5,071,828	12/10/1991	Greuter et al.	505	1	
RL	AM	3,985,281	10/12/1976	Diepers et al.	228	148	
RL	AN	5,038,127	08/06/1991	Dersch	335	216	
RL	AO	09/500,701 ✓	02/09/2000	Buczek et al.			
RL	AP	09/579,193 ✓	05/26/2000	Malozemoff et al.			
RL	AQ	3,763,552	10/09/1973	Brown et al.			

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
RL	AR	WO 99/35083	07/15/1999	PCT				✓
RL	AS	WO 99/25908 ✓	05/27/1999	PCT				✓
RL	AT	WO 98/58415 ✓	12/23/1998	PCT				✓
RL	AU	0 872 579 A1 ✓	10/21/1998	EPO				✓
RL	AV	WO 97/05669 ✓	02/13/1997	PCT				✓
RL	AW	0 387 525 A1	09/19/1990	EPO				✓

Examiner Signature 	Date Considered 12/14/01
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	